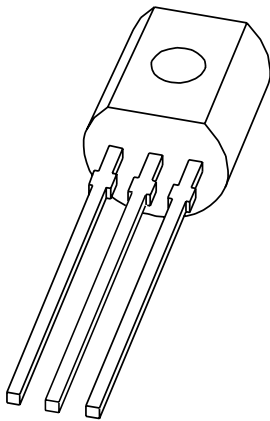


DATA SHEET



BC369

PNP medium power transistor;
20 V, 1 A

Product data sheet
Supersedes data of 2003 Nov 20

2004 Nov 05

**PNP medium power transistor;
20 V, 1 A**

BC369

FEATURES

- High current
- Two current gain selections.

APPLICATIONS

- Linear voltage regulators
- High side switches
- Supply line switches
- MOSFET drivers
- Audio pre-amplifiers.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–	–20	V
I_C	collector current (DC)	–	–1	A
I_{CM}	peak collector current	–	–2	A
h_{FE}	DC current gain			
	BC369	85	375	
	BC369-16	100	250	
	BC369-25	160	375	

DESCRIPTION

PNP medium power transistor (see “Simplified outline, symbol and pinning”) for package details.

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE
	PHILIPS	EIAJ	
BC369	SOT54	SC-43A	C369
BC369-16	SOT54	SC-43A	C36916
BC369-25	SOT54	SC-43A	C36925

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
BC369		1	base
		2	collector
		3	emitter

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BC369	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BC369-16			
BC369-25			

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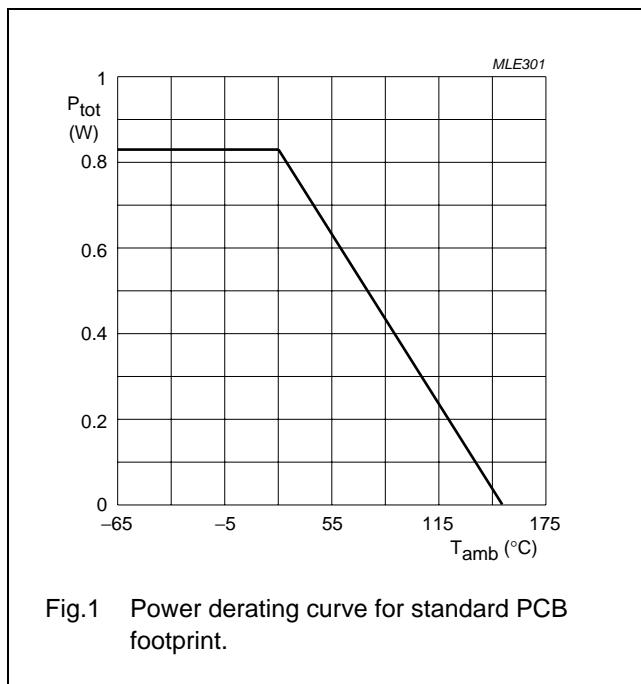
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–32	V
V_{CEO}	collector-emitter voltage	open base	–	–20	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–1	A
I_{CM}	peak collector current		–	–2	A
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; notes 1 and 2	–	830	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Notes

1. Refer to SOT54 (SC-43A) standard mounting conditions.
2. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; standard footprint for SOT54.



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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \leq 25\text{ }^\circ\text{C}$; notes 1 and 2	150	K/W

Notes

1. Refer to SOT54 (SC-43A) standard mounting conditions.
2. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; standard footprint for SOT54.

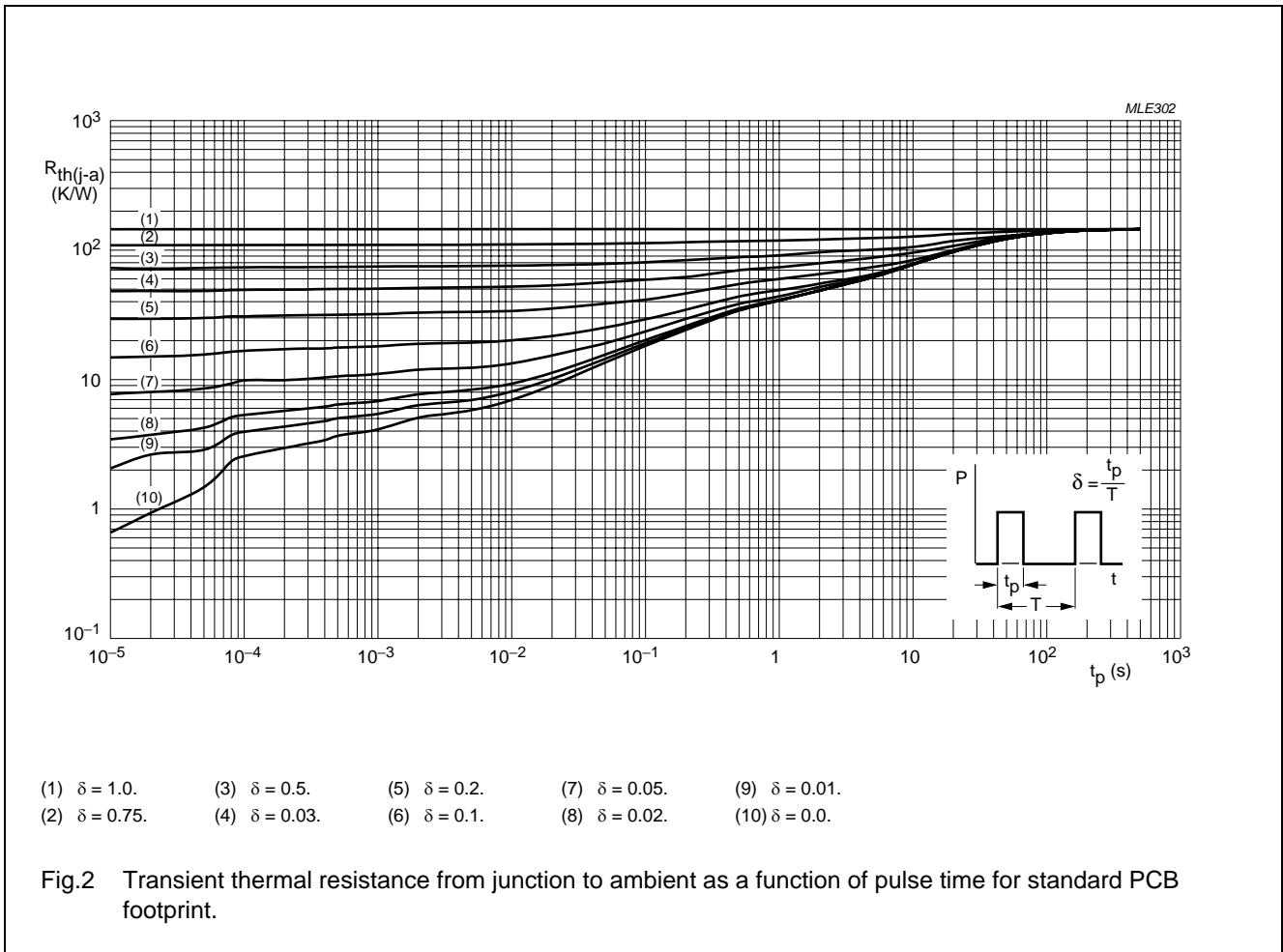


Fig.2 Transient thermal resistance from junction to ambient as a function of pulse time for standard PCB footprint.

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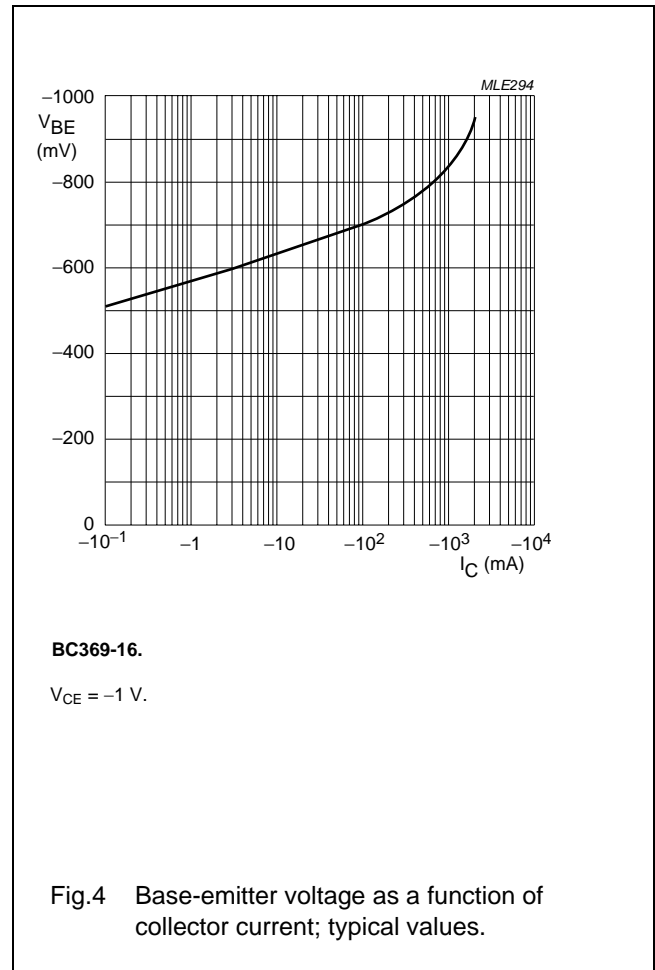
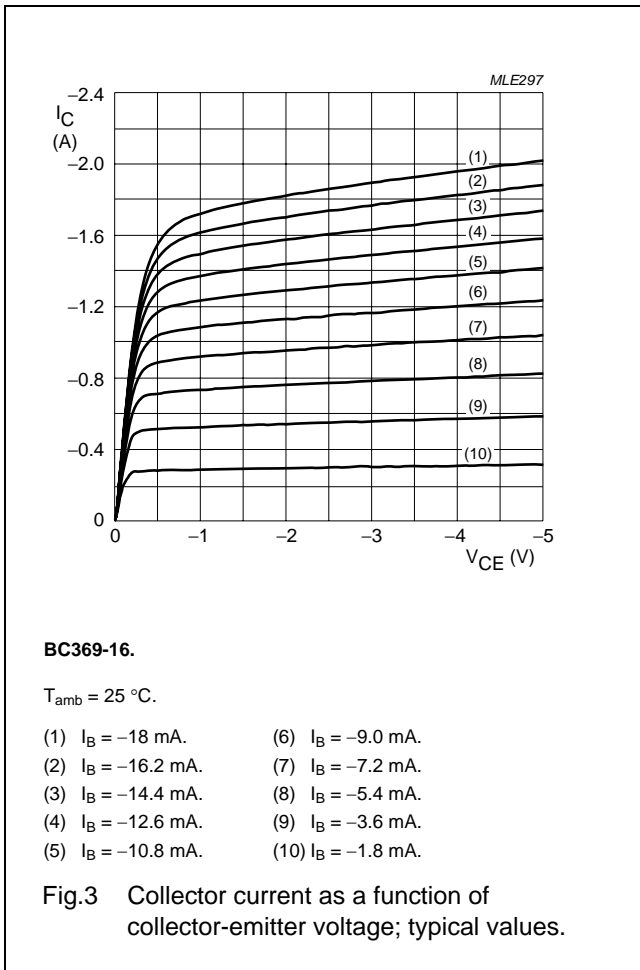
BC369

CHARACTERISTICST_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT																	
I _{CBO}	collector-base cut-off current	V _{CB} = -25 V; I _E = 0 A	-	-	-100	nA																	
		V _{CB} = -25 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μA																	
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A	-	-	-100	nA																	
h _{FE}	DC current gain	BC369	V _{CE} = -10 V; I _C = -5 mA	50	-	-																	
							V _{CE} = -1 V; I _C = -500 mA	85	-	375													
											V _{CE} = -1 V; I _C = -1 A	60	-	-									
															BC369-16	V _{CE} = -1 V; I _C = -500 mA	100	-	250				
																				BC369-25	V _{CE} = -1 V; I _C = -500 mA	160	-
V _{CEsat}	collector-emitter saturation voltage	I _C = -1 A; I _B = -100 mA	-	-	-500	mV																	
							V _{BE}	base-emitter voltage	V _{CE} = -10 V; I _C = -5 mA	-													
									V _{CE} = -1 V; I _C = -1 A	-	-	-1	V										
							C _c	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz	-	28	-	pF										
							f _T	transition frequency	V _{CE} = -5 V; I _C = -50 mA; f = 100 MHz	40	140	-	MHz										

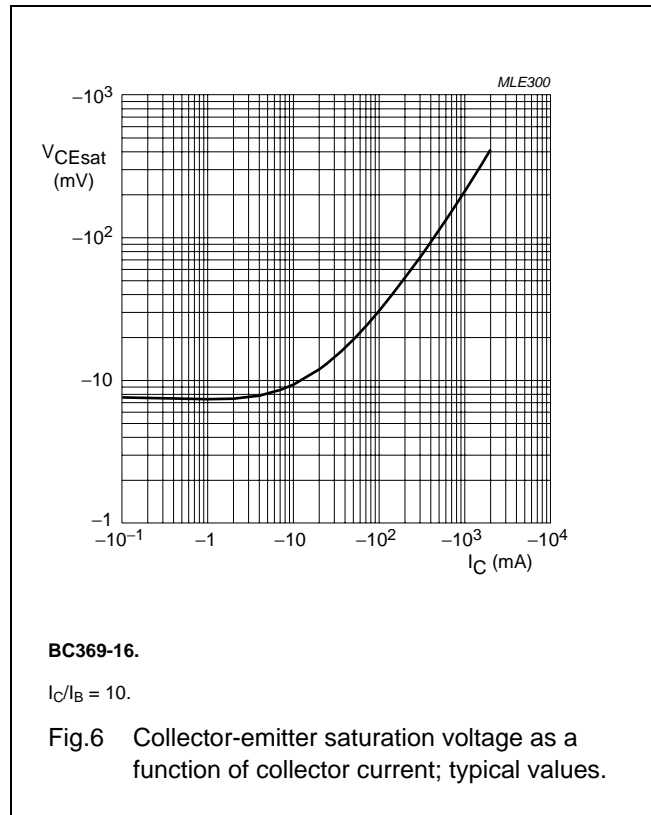
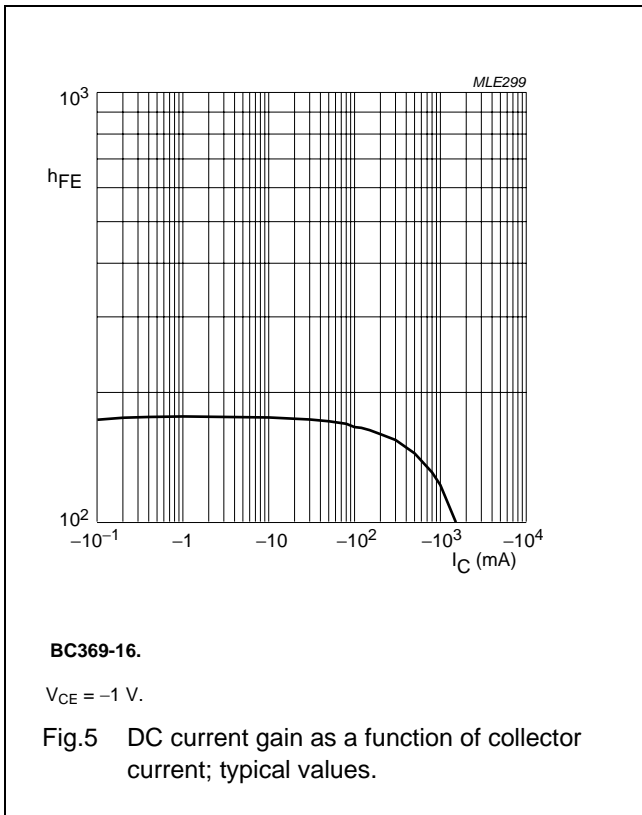
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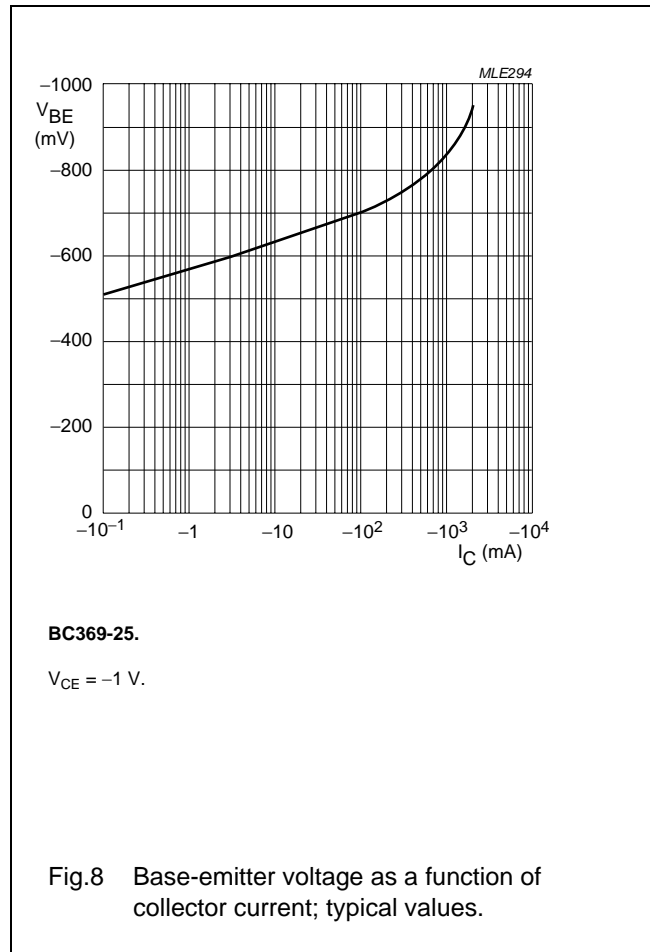
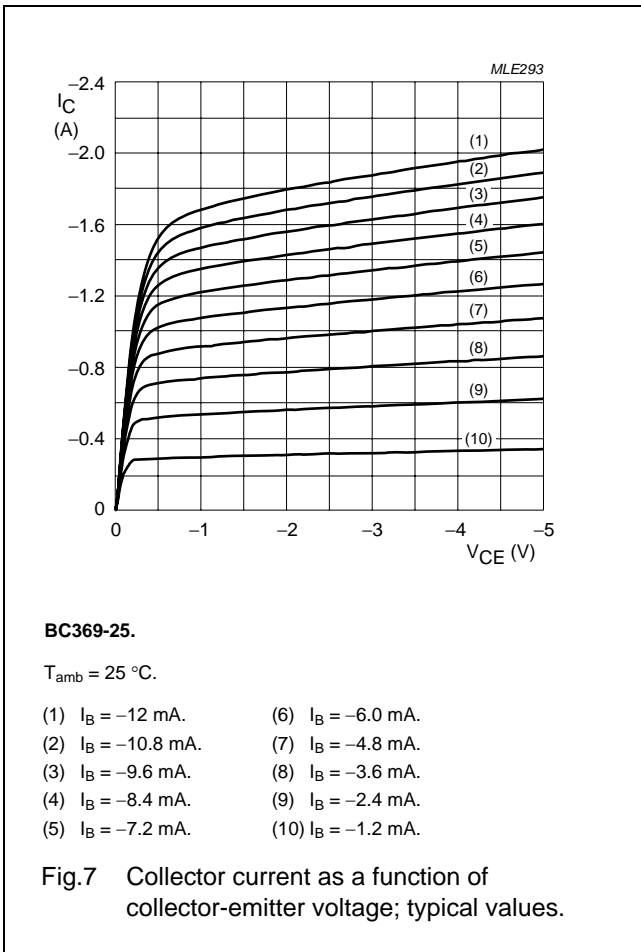
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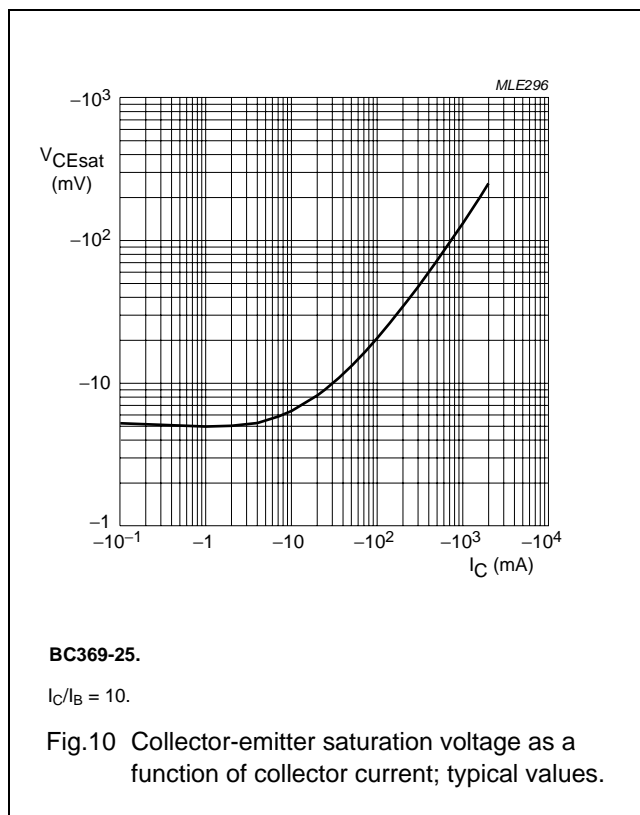
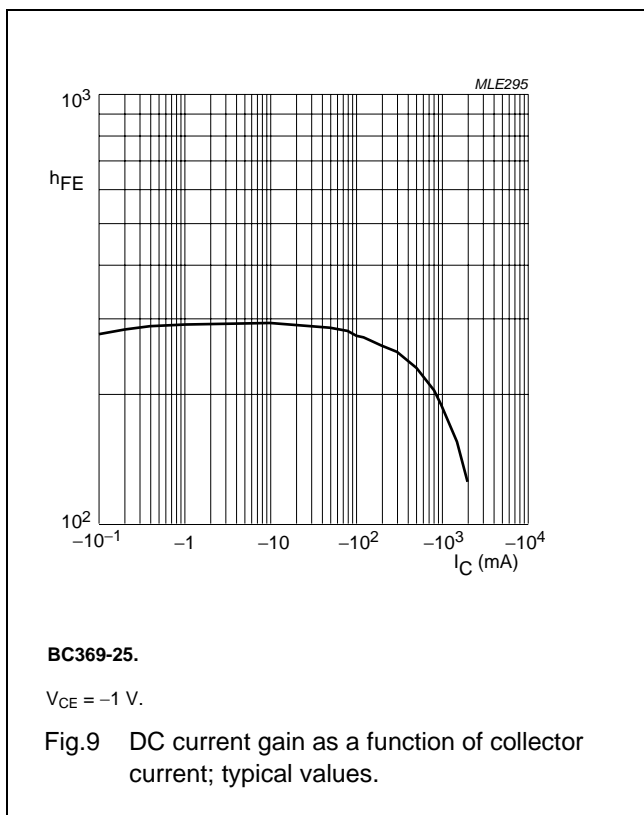
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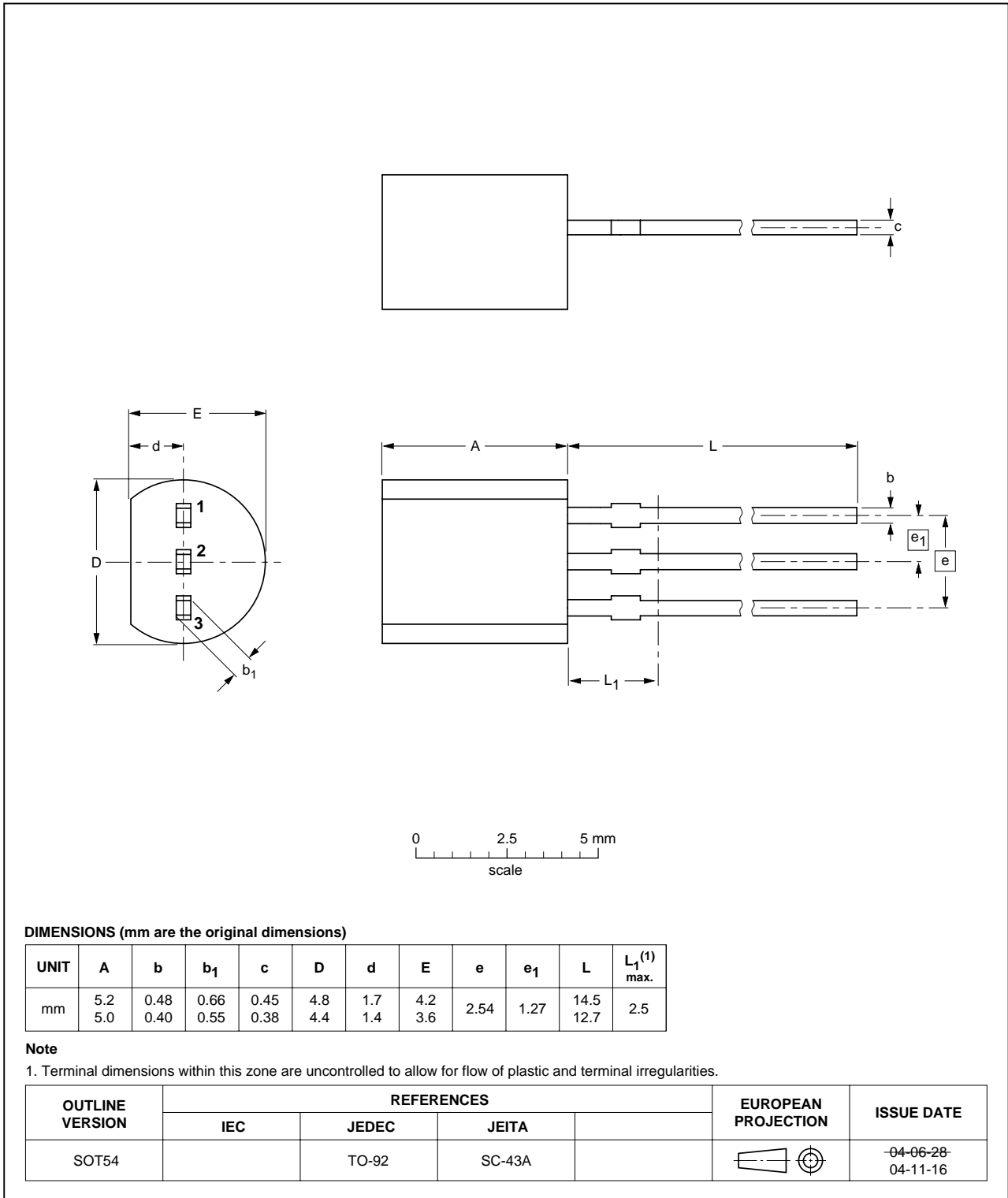
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



PNP medium power transistor;
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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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